

ERRATUM | APRIL 18 2011

Erratum: "Magnitude and sign control of lithography-induced uniaxial anisotropy in ultrathin (Ga,Mn)As wires" [Appl. Phys. Lett. 98, 083101 (2011)] **FREE**


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
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In the originally published version of this letter the sentence on page 2 starting with “In the whole temperature range,...” is incomplete. Complete it should read as follows: “In the whole temperature range, the uniaxial AMR coefficient [the first term in Eq. (2)] for the 1- μm -wide wires is by a factor of 1.5 to 2 times larger than that for the 20- μm -wide wire [the first term in Eq. (1)].”

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